Reference

1) Kauppinen, Christoffer. "Atomic layer etching of indium tin oxide." Journal of Vacuum Science & Technology A 42.2 (2024).

2) Mameli, Alfredo, et al. "Isotropic atomic layer etching of ZnO using acetylacetone and O2 plasma." ACS applied materials & interfaces 10.44 (2018): 38588-38595.

3) Karakaya, Canan, et al. "Thermogravimetric analysis of InCl3 sublimation at atmospheric pressure." Thermochimica -63.

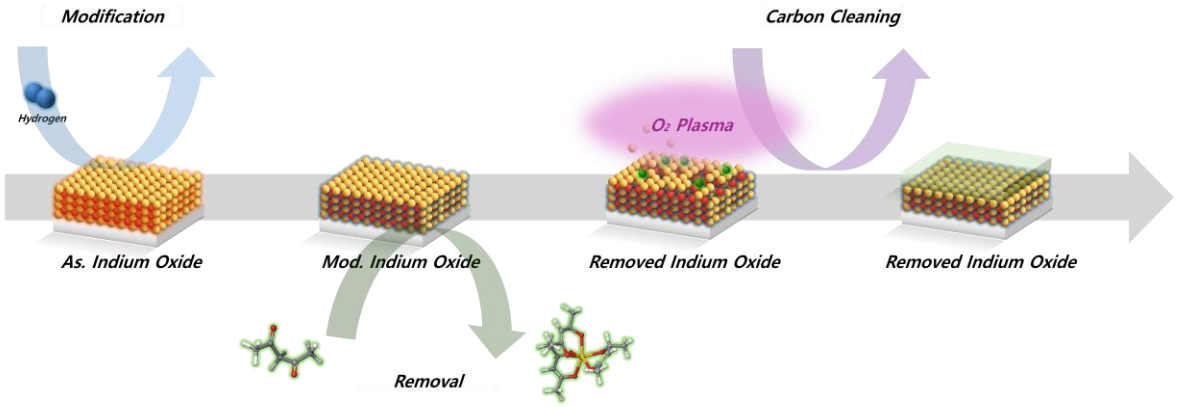

Figure 1. Schematic of proposed atomic layer etching process by using hydrogen modification and ligand addition reaction

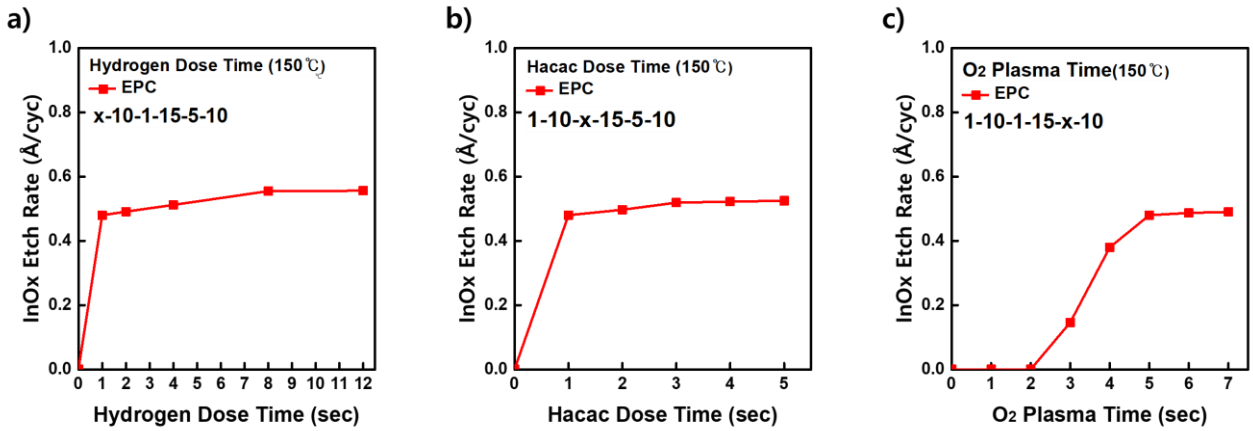

Figure 2. EPC Saturation curve as a function of hydrogen dose, Hacac dose, and O_2 plasma dose (a) Hydrogen Dose (b) Hacac Dose (c) Oxygen Plasma exposure

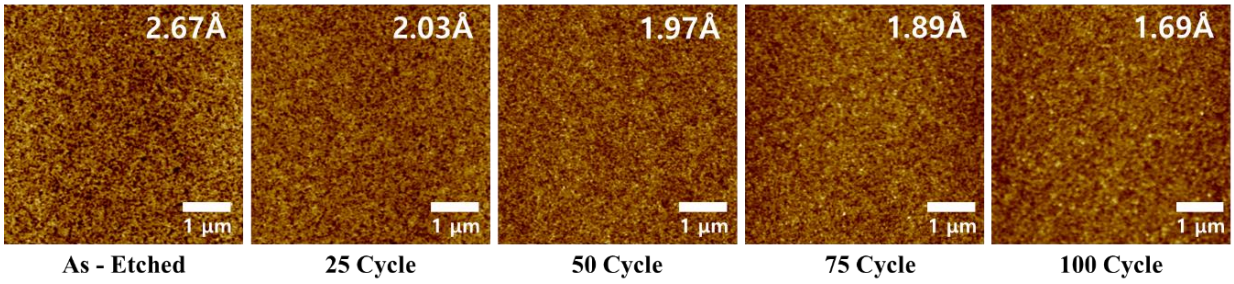

Figure 3. AFM images of 10 nm initial thickness InOx at 150°C for each etching cycle.